



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	1.8Ω@10V	0.34A
	2.1Ω@4.5V	

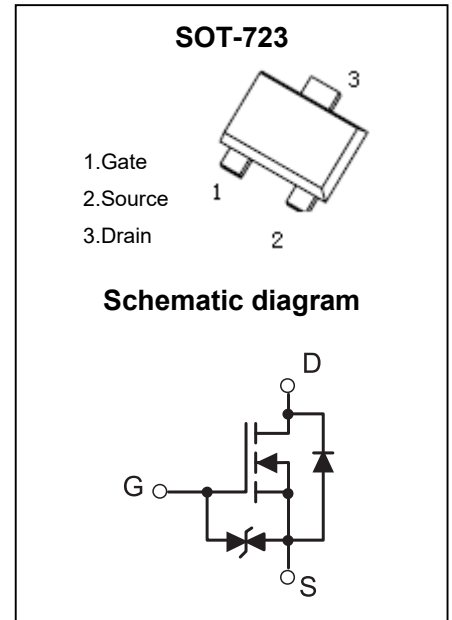
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- ESD Protected

Application

- Load Switch
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^{1,5}	I_D	0.34	A
Pulsed Drain Current ²	I_{DM}	1.3	A
Power Dissipation ^{4,5}	P_D	0.2	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

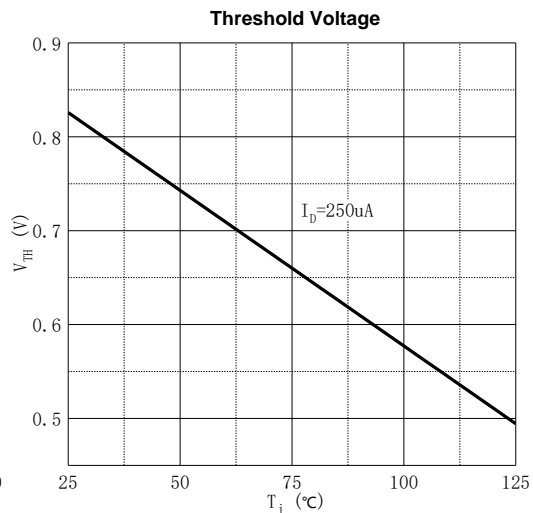
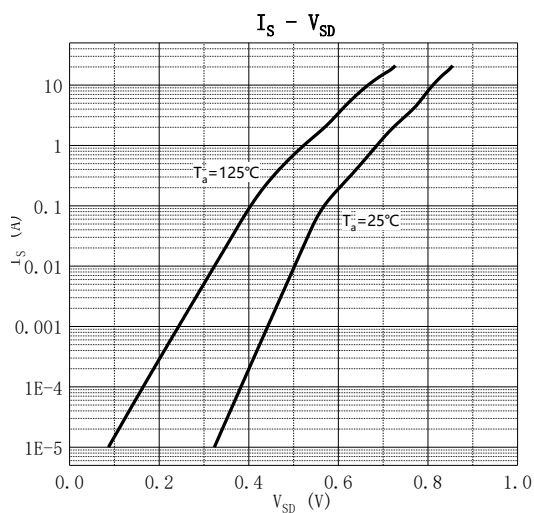
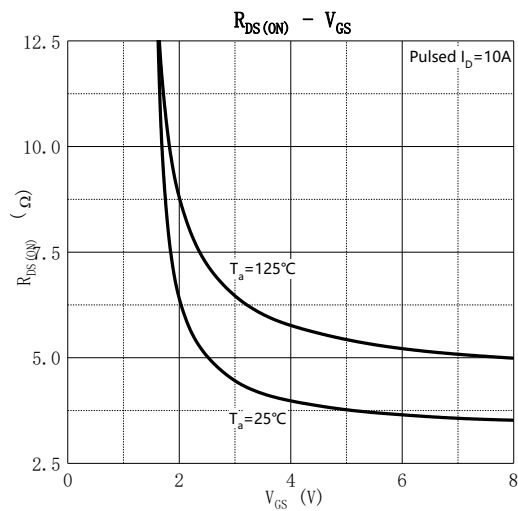
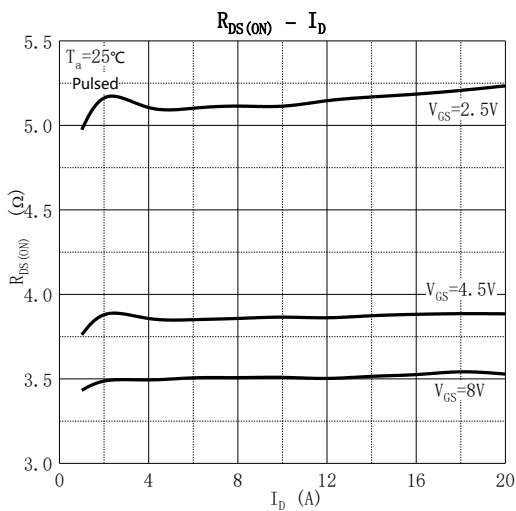
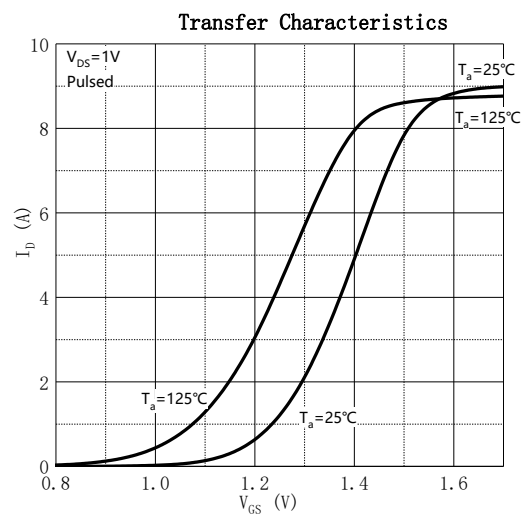
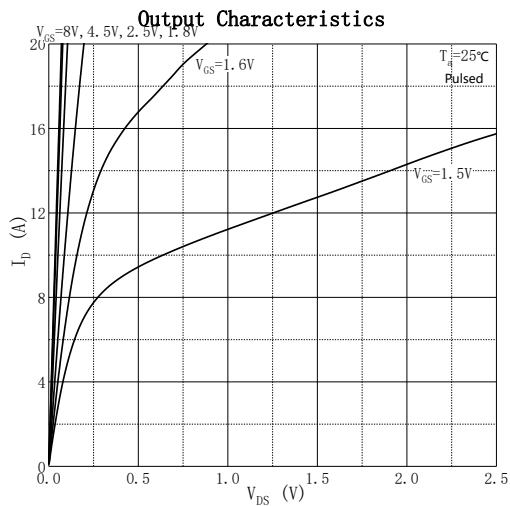
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±5	μA
On Characteristics³						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2.5	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 0.34A		1.8	2.5	Ω
		V _{GS} = 4.5V, I _D = 0.2A		2.1	3.0	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		16.6		pF
Output Capacitance	C _{oss}			4.7		
Reverse Transfer Capacitance	C _{rss}			2.2		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		45		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 10V, I _D = 0.3A		1.3		nC
Gate-source Charge	Q _{gs}			0.16		
Gate-drain Charge	Q _{gd}			0.47		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, R _L = 100Ω, R _G = 3Ω		3.8		ns
Turn-on Rise Time	t _r			2.9		
Turn-off Delay Time	t _{d(off)}			14		
Turn-off Fall Time	t _f			8		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	V _{GS} = 0V, I _S = 0.2A			1.2	V

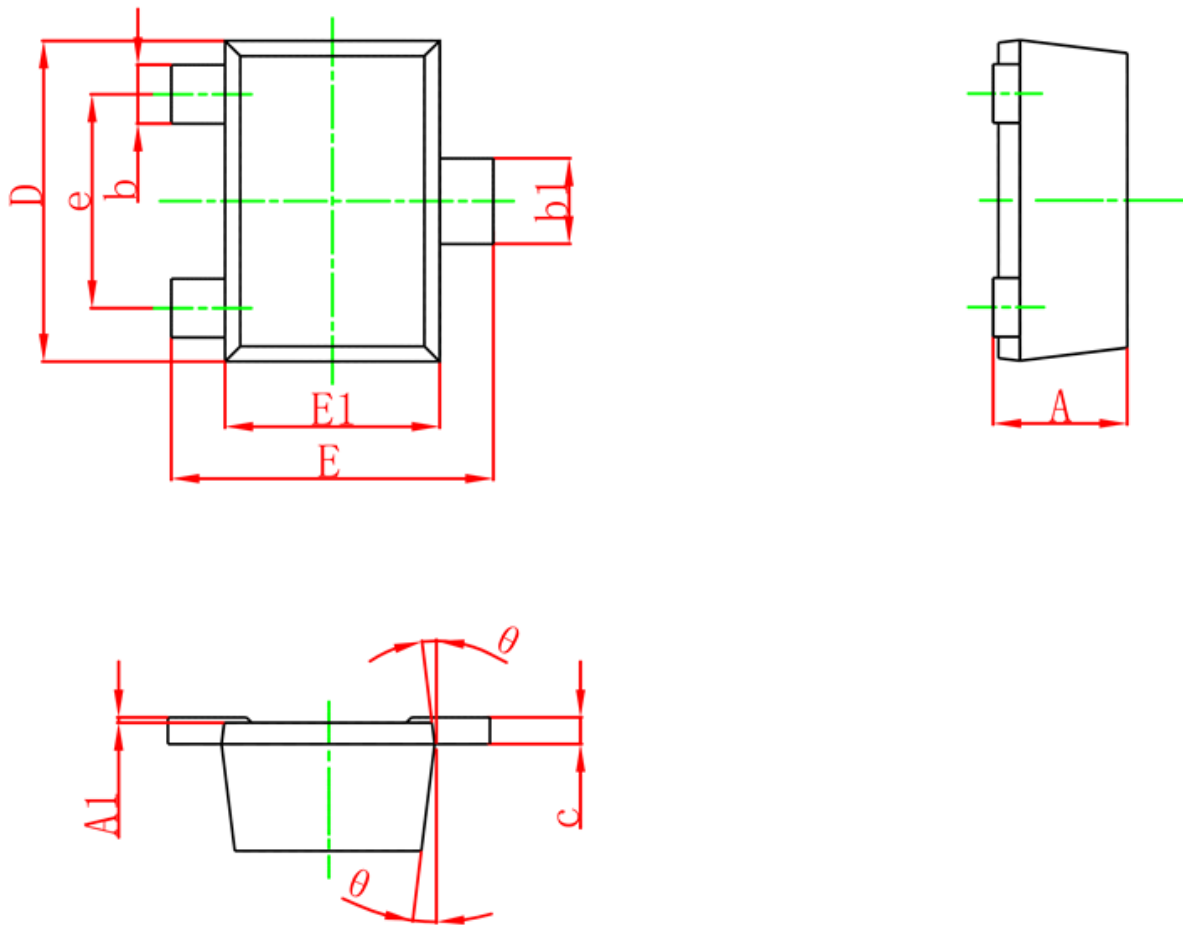
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 4.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Characteristics



SOT-723 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.340	0.500	0.013	0.020
A1	0.000	0.050	0.000	0.002
b	0.150	0.270	0.006	0.011
b1	0.200	0.370	0.008	0.015
c	0.060	0.160	0.002	0.006
D	1.100	1.300	0.043	0.051
E	1.100	1.300	0.043	0.051
E1	0.700	0.900	0.028	0.035
e	0.8TYP		0.031TYP	
θ	8°REF		8°REF	